DESIGN CONSTRUCTION AND TESTING OF A RAPID LIGHT CHANGE PROXIMITY DETECTOR SWITCH

## $B Y$

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## CERTIFICATION

I hereby certify that this project work was carried out by Mr Obotee Stephen of the Department of Electrical/Computer Engineering, Federal University of Technology, Minna, Niger State, Nigeria
H.O.D ${ }^{9} \mathrm{~S}$; signature

## Supervisor's signature



External Examiner's sign

Date

Date
$\frac{771 \mid 2 r}{\text { Date }}$

## DEDICATION

This project work is dedicated to the lord Almighty, my brother Mr. S. Obotee and my beloved Sister Mrs. Juliet Okitiakpe.

## ACKNOWLEDGEMENT

First and foremost, I acknowledge the special work of the lord for the guidance and protection which he has been giving to me. For if not for the lord's sake, I wouldn't have lived to see and construct this project.

Secondly, special thanks goes to my project supervisors Engr. Kenneth Pinne, Engr. A Shehu and our Head of Department Dr. Engr. Y.A. Adediran for the untiring efforts which they have made during the project building, testing and in the writing of the associated report.

My greatest gratitude goes to my brother Mr. Samuel Obotee 'and sister Mrs. Juliet Okitiakpe, for the financial backing which they have been giving to me.

Also, I owe my colleagues in struggle Mr Emegere Sylvester, Mr. Elisha, Mr. Egbejuma William, Mr Dim Simon and Mr. Kingsley Abiala, a series of thanks for their individual contribution to make this project work a success.

Those that contributed to this project, whose names are not mentioned here, due to space, time or the human short memory, should forgive me. The lord almighty should reward them all Amen.

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## ABSTRACT

This project work concentrates on the design, construction and testing of a rapid light change proximity detector switch.

The switch uses a photocell as its sensor. The sensed signal is sent to an amplifier. The resultant signal from this circuit is rectified. The rectified version of this signal is used to bias a transistor. This causes a relay contact to make. Hence triggering the appropriate circuit into conduction.

The circuit could be used in intruder alarm systems or in certain other application where proximity detection is required.

## CHAPTER ONE

### 1.1 INTRODUCTION

The rapid light change proximity detector switch is better described than defined. It is a kind of circuit that is used to trigger another circuit. The circuit uses a photocell as its sensor. It is not a light operated switch of the type which responds to some particular ambient light level. It differs from the common proximity switches in that while it uses a photocell as its sensing element, the common proximity detectors uses infrared rays. It will for example trigger if a torch is shone on or near the photocell or if someone passing in front of the Unit casts a shadow onto the photocell the unit on the other hand is unaffected by natural slow changes in light level.

In its simplest form it is a light change detector which uses a photoresistor. The photoresistor (photocell) is a component whose resistance increase when light falls on it. And hence creating a low resistance path for the flow of current. But when darkness falls, the behaviour is reversed. This property of the photoresistor enables it to control the flow of current into another circuit.

This simple switch can be employed in any circuit where proximity detection is the watch word. It has a wide range of safety/security applications. In the area of safety for example, the switch could be used to design a circuit that will issue a warning signal to anybody that gets close to a dangerous area, This is achieved by making the switch to operate a tape recorder or computer in which a warning signal has formerly been recorded or programmed.

In the industry it could be used to trigger a counting circuit in a bid to counting the number of items produced by a particular machine. In the area of security it could be used to trigger an alarm circuit which will serve as a warning to soldiers on guard that the enemies are close. And in residential usage it could be employed to trigger an alarm circuit which will draw the attention of the inhabitants of the house.

In the project work, the simple circuit to be triggered is the alarm ciruit.

### 1.1 METHOD OF OPERATION

When the shadow of someone passing in fronts of the photocell falls on the cell or when a torch light is shown on the photocell, there is a decrease on resistance of the photoresistor which causes a rapid change in the output voltage from the photocell circuit. This change in voltage will be passed to the input of the amplifier and will appear at the output. The output from the operational amplifier is coupled with a capacitor to a rectifying and smoothening circuit consisting of diodes and capacitor respectively

When the unit is activated, the positive bias produced across the smoothing capacitor is sufficient to bias the transistor into conduction so that it energises the relay coil of the circuit which is required to be activated. In this case the circuit to be triggered is an alarm circuit.

### 1.2 LITERATURE REVIEW

Proximity detection has been achieved at one time or the other in the past in various ways. Differences lies in the various forms of detecting element (sensor) or circuit used. And also on the various circuits to be triggered. The first detector that comes to mind is that which uses infra-red radiation. This is a kind of line detector. An intruder could bypass the line, knowing that there is such a detector in place. This also has a disadvantage in the sense that infra-red radiations are being absorbed by alcohol vapour

The other form of detector known is that which uses a photoresistor (photocell). This is a form of volume detector. This has the advantage of the fact that the intruder would have to pass through the volume occupied by the beam of light which used be interrupted for the circuit to be triggered. And it cannot be absorbed by alcohol vapour. The disadvantage of this form of detector lies in the fact that it responds to some particular ambient light level. Or it may respond to natural slow changes in light level.

Now, this project is aimed at designing a detector that does not respond to natural slow changes in light level, and does not respond to light of a particular ambient light level;


Fig1. Photocell/potenbial divider circuit

## CHAPTER TWO

### 2.0 DESIGN CALCULATION/CONSIDERATION

The art of designing is to select the most suitable solution on the basis of size, cost and performance (electronics digest, winter 1981).

### 2.1 DESIGN CALCULATION FOR THE PHOTOCELL (SENSOR)



Let the resistance of the photoresistor $($ photocell $)=30 k$
Let the reference voltage be 6 V
Now with a supply voltage of 12 V ,
We have that from voltage divider principle (equation 3):

$$
\begin{aligned}
& \frac{R_{1}}{R_{1}+30} \times 12=6 \\
& 12 R_{1}=6 R_{1}+180 \\
& 6 R_{1}=180 \\
& R_{1}=30 K
\end{aligned}
$$

But for reason of availability of component 27 K was selected.
Also, from the diagram above;
Let $R_{3}=47 \mathrm{~K}$

$$
\begin{aligned}
& \mathrm{Vcc}=12 \mathrm{~V} \\
& \mathrm{Vref}=6 \mathrm{~V}, \quad \mathrm{R} 4=?
\end{aligned}
$$

The from voltage divider principle,
$\frac{R_{4}}{R_{4}+47} \times 2=6$
$12 R_{4}=6 R_{4}+6 \times 47$
$6 R_{4}=6 \times 47$
$R_{4}=47 K$

### 2.2 DESIGN CALCULATION FOR THE COMPARIATOR CIRCUIT

Now for high sensibility a high gain is needed let the gain required for this design $=60 \mathrm{~dB}$.

Let the input resistance ' $\mathrm{R}_{1}{ }^{\prime}=10 \mathrm{~K}$
Now from the gain relation for the operational amplifier, we have that the gain is in voltage $A v=\frac{R F}{R_{1}}$.

Where $R_{f}$ if the feedback resistor value.
Now, from the decibel story;

$$
\begin{equation*}
\mathrm{XdB}=20 \log \text { (gain ratio) } \tag{V}
\end{equation*}
$$

Where $X=$ gain in decibel. $=60$ in this case,

$$
\text { gain ratio }=\frac{V_{2}}{V_{1}}=\frac{R F}{R_{1}}
$$

By substituting into equation [v], We have that.

$$
60 \mathrm{~dB}=20 \log _{10}\left[\frac{R F}{10^{3}}\right]
$$

$$
3=\log _{10}\left[\frac{R F}{10^{3}}\right]
$$

$$
10^{3}=\frac{R F}{10^{3}}
$$

$$
\mathrm{RF}=\quad 10^{3} \times 10^{3}=10^{3}=1 \mathrm{M} \Omega
$$

Hence the feedback resistor required to obtain this gain was chosen as $1 \mathrm{M} \Omega$.

The slew rate of the op-amp $\mu \mathrm{A} 741=0.5$
gain bandwidth $=1$ to 1.5 MHZ
Noise Voltage At $1 \mathrm{KHZ}=20$ to 50 not usually specified on data books.
Maximum current $=1.5 \mu \mathrm{~A}$.

### 2.3 THE PIN LAYOUT OF $\mu \mathrm{A} 741$



> FIg Pin Layout of MA741

### 2.4 THE INTERNAL ARCHITECTURE OF $\mu$ A741 IS AS SHOWN BELOW (SIMPLIFIED VERSION):

fig 4
Internal

architccure of MAT 41

Shown above, is the simplified schematic diagram of the 741 . This circuit is equivalent to the 741 and many later generation opamps. The input stage is a differential amp. Using php transistors $\left(Q_{1}\right.$ and $\left.Q_{2}\right)$. To get a high CMRR, a current mirror $\left(Q_{13}\right.$ and $\left.Q_{14}\right)$ sources tail current to the different amp. Also to get a high a voltage gain possible for the diff. amp a current mirror load is used $\mathcal{Q}_{1}$ and $Q_{4}$ ). The output of the diff. $\operatorname{amp}$ (collector of $Q_{2}$ ) drives an emitter follower $Q_{5}$. This stage steps up the impedance level to avoid loading down the diff. amp. The signal output of $Q_{5}$ goes to $Q_{6}$, which is a class $B$ driver, incidentally, the plus sign on the collector of $Q_{5}$ means that it is connected to the $+V c c$ supply. Similarly the minus sign on the bottoms of $R_{2}$ and $R_{3}$ mean that these are connected to earth supply.

## DESIGN CALCULATION AND CONSIDERATION FOR THE AMPLIFIER CIRCUIT

Now the output signal from the rectifier circuit taken across capacitor $\mathrm{C}_{6}$ is a positive going signal and hence it requires a transistor which uses a positive signal for forward biasing its base a emmitter junction. The appropriate transistor to use here is an NPN transistor, In this position the BC109C (an NPN transistor) was found to be appropriate. It has:

1. $\mathrm{A} V C E O(\max ) \vee$ of 20 V
2. $\mathrm{A} V C B O$ (max) of 30 V
3. A VEBO (max) OF 5 V
4. Maximum collector current Ic $\max =100 \mathrm{~mA}$
5. Ртот $\max$ of 300 mw
6. $\operatorname{HFE}(\beta)(520) 2 \mathrm{~mA}$

It is a low noise high gain amplifier.
Now, the maximum base current of $\mathrm{BC} 109 \mathrm{C}=I \beta=\frac{I c}{\beta}=\frac{100}{520}=0.1923 \mathrm{~mA}$.
Now, the maximum current that could be supplied by the selected op Amp is $1.5 \mu \mathrm{~A}$. So the NPN transistor selected is in line. The RLA 4088 requires a current of 10 MA a voltage range of $(6-12)$ volts. It has a pair of contacts, normally open and normally closed. In circuit, one of the normally open contacts is connected in such a way for it to maintain supply across the relay coil when triggered.

### 2.5 DESIGN CALCULATION OF THE ALARM CIRCUIT

The popular 4011Ic package used in this project work actually consists of (MOS logic gates. The complementary metal oxide semiconductor logic gates are very useful in implementing simple multivibrator circuits. A multivibrator may be monostable, Bistable or Astable. It is monostable when it has only pne stable state. It is bistable when it has two stable states. And it is said to be Astable,
when it is not stable in any of its states. In the Astable state it does not require an external trigger pulses for it to be change from one states to the other.

This 4011 package consists of four CMOS NAND gates.
The circuit of the alarm shown consist of a timing circuit (RC circuit). The value of the frequency determining component are obtained as follows:

Let the frequency of operation $=600 \mathrm{HZ}$ (chosen within the audio freq range of $20 \mathrm{KHZ}-16000 \mathrm{KHZ}$ )

$$
\text { Let } R_{3}=100 k
$$

$$
C_{2}=?
$$

:. From the relation:
$F=\frac{1}{2 t_{1}}=\frac{1}{2.2 \tau}-(W)$
where $T=R x C x$
$\therefore F=\frac{1}{2.2 R x c x}$
by substitution,
$600=\frac{1}{2.2 \times 100 \times 10^{3} \times C x}$
$C x=\frac{1}{600 \times 2.2 \times 100 \times 10^{3}}$
$\approx 8 n$
so for the fast astable, Cx was chosen to be 10 n
for the slow astable.
Let $R_{5}=6.8 \mathrm{M} \Omega$

$$
C_{3}=?
$$

From the same relation

$$
\begin{aligned}
f & =\frac{1}{2.2 T} \\
T & =R x C x=\text { period } \\
600 & =\frac{1}{2.2 R x C x} \\
& =\frac{1}{2.2 \times 68 \times 10^{6} \times C_{3}} \\
C_{3} & =\frac{1}{2.2 \times 6.8 \times 10^{6} \times 600} \\
& =110 \mathrm{n}
\end{aligned}
$$

for the reason of availability of component,
$C_{3}=100 \mathrm{nF}$

### 2.7 THE INTERNAL ARCHITECTURE OF 4011B



Fig 5 Internal architecture
Propagation delay at $5 \mathrm{v}=125 \mathrm{~ns}$
Propagation delay at $10 v=50 n s$
Propagation delay at $15 \mathrm{v}=40 \mathrm{~ns}$

## CHAPTER THREE

### 3.0 CONSTRUCTION AND TESTING

The project components were mounted on a veroboard. The size of the board to be used was arrived at after a careful consideration of the number of components to be used and the amount of space which they might likely occupy.

First the components themselves were examined and cross checked against their individual specifications. The lerminals of the transistor were Identified. The identification of the fransistor and capacitor's terminals were done with extra care. This is because if a transistor is connected with the wrong terminal in circlit it burns immediately (It become hot and finally burns out -).

In the second place, the position to be occupied by each components on the veroboard were marked one with the aid of a pencil. The positive the and negative potential to be used on the veroboard was marked as shown on the sketch below:


The marking was done for it to serve as a guide during connection. The terminals of the components which have been installed, were trimed to avoid a short circuit.

Lastly the component were soldered to the veroboard. Care was taken for not allowing heat to destroy some of the circuit components (heat from the hot
soldering iron). The veroboard was cleaned first before the soldering procedure started. This was to avoid the formation of a cold joint

The complete circuil diagram of the rapid light change proximity detector switch and the schematic diagram are as shown below:
$\perp \| I I J \mid J$ WG甘 IV



3.4.1 COMPONENT SPECIFICATION AND COSTING

| RESISTORS |  |  |
| :--- | :--- | :--- |
| COMPONENT | SPECIFICATION | COST(A) |
| Resistor R1 | $27 \mathrm{~K} \Omega$ | 10.00 |
| Resistor R2 | $10 \mathrm{~K} \Omega$ | 10.00 |
| Resistor R3 | $47 \mathrm{~K} \Omega$ | 10.00 |
| Resistor R4 | $47 \mathrm{~K} \Omega$ | 10.00 |
| Resistor R5 | $10 \mathrm{~K} \Omega$ | 10.00 |
| Resistor R6 | $3.3 \mathrm{~K} \Omega$ | 10.00 |
| Resistor $\mathrm{R}^{1} 1$ | $12 \mathrm{~K} \Omega$ | 10.00 |
| Resistor $\mathrm{R}^{1} 2$ | $12 \mathrm{~K} \Omega$ | 10.00 |
| Resistor $\mathrm{R}^{1} 3$ | $6.8 \mathrm{~K} \Omega$ | 10.00 |
| Resistor $\mathrm{R}^{1} 4$ | 220 K | 180 K (Variable) |
| Resistor $\mathrm{R}^{1} 5$ |  | 10.00 |
|  |  | 10.00 |


|  |  | CAPACITORS |
| :--- | :--- | :--- |
| COMPONENT | SPECIFICATION | COST(N) |
| Capacitor C1 | $330 \mu \mathrm{~F}(10 \mathrm{v})$ | 20.00 |
| Capacitor C2 | 100 n | 20.00 |
| Capacitor C3 | 220 n | 10.00 |
| Capacitor C4 | 8.2 p | 10.00 |
| Capacitor C5 | $10 \mu \mathrm{~F}$ | 15.00 |
| Capacitor C6 | 470 n | 10.00 |
| Capacitor C1 | $10 \mu \mathrm{~F}$ | 15.00 |
| Capacitor $C_{2}^{\prime}$ | 100 n | 10.00 |
| Capacitor filter cap | $2200 \mu \mathrm{~F}$ | 40.00 |


| ASSORTED COMPONENT TYPES |  |  |
| :--- | :--- | :--- |
| COMPONENT | SPECIFICATION | COST(A) |
| Transistor | BC109B | 30.00 |
| MOSFET | VN66AF | 250.00 |
| ICI | CD4011B | 70.00 |
| OpAmp | HA741 | 40.00 |
| LDR | - | 150.00 |
| LED | -4 PCS | 40.00 |
| Transformer | $220 \mathrm{~V} / 12 \mathrm{~V}$ | 150.00 |
| Veroboard | - | 100.00 |
| Bread Board | - | 450.00 |
| Dissoibering Pump | - | 100.00 |
| Diode | 120.00 |  |
| Relay |  | 80.00 |
| On/Off Switch |  | 70.00 |
| Speaker |  | 150.00 |
| Wooden Casing |  | 200.00 |
| Connecting Wire |  | 60.00 |
| Soldering Lead |  | 20.00 |
| Typing Printing/Binding |  | $1,500.00$ |
| Transportation |  | $2,000.00$ |
| NET TOTAL: |  |  |

This prices above are valid at the time of my design construction.

### 3.4 SUGGESTION ON HOW TO IMPROVE ON THIS PROJECT

Inspite of the wide use to which the proximity detector switch could be put, there is still the need to improve on it so that.

1. It can cover a wider area of application
2. The circuit to he friggered on will switch of after some time.
3. The reset circuit should be authomized

For it to cover a wider area, the sensitivity should de increased. For the reset circuit to be automatic a triming circuit should be included. This will enable it to trigger off after some time.

### 3.5 MECHANICAL CONSTRUCTION DIAGRAM



## CHAPTER FOUR

### 4.1 CONCLUSION

The practical work was carried out exactly as designed. At the end of the practical construction. It was observed that the unit responded to light levels of all intensities. But what differs is the distance of the source from the sensor. When a touch light is shone on it or when the shadow of someone passing in front of the unit at a distance of about two to three feet from the sensor falls on it, a clicking sound is heared. And the alarm signal, which serves as the test circuit in the design of this project work, comes on.

In a sentence, the produced project work meets the design or proposed goal.

### 4.2 RECOMMENDATIONS

The project work which forms a part of the university education is of many benefits to the students. But it is not being encouraged by the school authorities for effective handling of the project work by students, I recommend that:

1. Components should be provided to the students. This will enable them to embark on the construction of Many projects. Thereby strengthening their hands. This will enable them to produce better projects.

## REFERENCES

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## APPENDIX A

| $\mathrm{R}_{\mathrm{f}}$ | $=$ Feedback Resistor |
| :--- | :--- |
| CMMR | $=$ Common mode rejection ratio |
| $\mathrm{V}_{\text {CEO }}$ | $=$ Max. collector emitter leakage current |
| $\mathrm{V}_{\text {CBO }}$ | $=$ Max. collector base leakage current |
| $\mathrm{V}_{\text {CBO }}$ | $=$ Max. base emitter leakage current |
| $\mathrm{P}_{\text {TOT }}$ | $=$ Max. Peak too peak power |
| $H_{\text {fa }} \beta$ | $=$ Common emitter current gain |
| RLA | $=$ Relay |
| CMOS | $=$ Complementary metal oxide semiconductor |
| $N / C$ | $=$ Non connected |
| $V_{\text {ret }}$ | $=$ Reference voltage |

